

IN THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1-23. (Canceled)

24. (Currently amended) A semiconductor device comprising:

a semiconductor film;

a pair of first impurity regions being formed in the semiconductor film;

an active region formed between the pair of first impurity regions in the semiconductor film;

at least two second impurity regions formed in said semiconductor film between the pair of first impurity regions;

at least one channel region between the at least two second impurity regions,

boundaries between the channel region and the at least two second impurity regions extend in a direction along a carrier flow direction of the channel region,

a floating gate formed over and insulated from the active region; and

a control gate formed over and insulated from the floating gate,

wherein the floating gate overlaps a boundary between at least one of the pair of the first impurity regions and the at least two second impurity regions.

25. (Currently amended) A semiconductor device according to claim 24, wherein the at least two second impurity regions ~~has~~ have a striped shape.

26-27. (Canceled)

28. (Previously presented) A semiconductor device according to claim 24, wherein an electronic device mounting the semiconductor device is any one of a mobile computer, a head-mounted display, a video camera, a cellular phone, a digital camera, a rear type projector, a front type projector.

29. (Currently amended) A semiconductor device comprising:

a NOR type circuit having a plurality of memory transistors, the memory transistor comprising:

a semiconductor film;

a pair of first impurity regions being formed in the semiconductor film;

an active region formed between the pair of first impurity regions in the semiconductor film;

at least two second impurity regions formed in said semiconductor film between the pair of first impurity regions;

at least one channel region between the at least two second impurity regions,

boundaries between the channel region and the at least two second impurity regions extend in a direction along a carrier flow direction of the channel region,

a floating gate formed over and insulated from the active region; and

a control gate formed over and insulated from the floating gate,

wherein the floating gate overlaps a boundary between at least one of the pair of the first impurity regions and the at least two second impurity regions.

30. (Currently amended) A semiconductor device according to claim 29, wherein the at least two second impurity regions ~~has~~ have a striped shape.

31-32. (Canceled)

33. (Previously presented) A semiconductor device according to claim 29, wherein an electronic device mounting the semiconductor device is any one of a mobile computer, a head-mounted display, a video camera, a cellular phone, a digital camera, a rear type projector, a front type projector.

34. (Currently amended) A semiconductor device comprising:

- a NAND type circuit having a plurality of one memory transistor, the memory transistor comprising:
 - a semiconductor film;
 - a pair of first impurity regions being formed in the semiconductor film;
 - an active region formed between the pair of first impurity regions in the semiconductor film;
 - at least two second impurity regions formed in said semiconductor film between the pair of first impurity regions;
 - at least one channel region between the at least two second impurity regions, boundaries between the channel region and the at least two second impurity regions extend in a direction along a carrier flow direction of the channel region,
 - a floating gate formed over and insulated from the active region; and
 - a control gate formed over and insulated from the floating gate,

wherein the floating gate overlaps a boundary between at least one of the pair of the first impurity regions and the at least two second impurity regions .

35. (Currently amended) A semiconductor device according to claim 34, wherein the at least two second impurity regions ~~has~~ have a striped shape.

36-37. (Canceled)

38. (Previously presented) A semiconductor device according to claim 34, wherein an electronic device mounting the semiconductor device is any one of a mobile computer, a head-mounted display, a video camera, a cellular phone, a digital camera, a rear type projector, a front type projector.

39. (Currently amended) A semiconductor device comprising:

- a semiconductor film;

- a pair of first impurity regions being formed in the semiconductor;

- an active region formed between the pair of first impurity regions in the semiconductor film;

- at least two second impurity regions formed in said semiconductor film between the pair of first impurity regions;

- at least one channel region between the at least two second impurity regions,

- a floating gate formed over and insulated from the active region; and

- a control gate formed over and insulated from the floating gate,

wherein the at least two second impurity regions ~~has~~ have a dot-like shape or an elliptical shape;

wherein the floating gate overlaps a boundary between at least one of the pair of the first impurity regions and the at least two second impurity regions.

40. (Canceled).

41. (Previously presented) A semiconductor device according to claim 39 further comprising a substrate, wherein the semiconductor film is formed over the substrate.

42. (Canceled).

43. (Previously presented) A semiconductor device according to claim 39, wherein an electronic device mounting the semiconductor device is any one of a mobile computer, a head-mounted display, a video camera, a cellular phone, a digital camera, a rear type projector, a front type projector.

44. (Currently amended) A semiconductor device comprising:

a NOR type circuit having a plurality of memory transistors, the memory transistor comprising:

a semiconductor film;

a pair of first impurity regions being formed in the semiconductor film;

an active region formed between the pair of first impurity regions in the semiconductor film;

at least two second impurity regions formed in said semiconductor film between the pair of first impurity regions;

at least one channel region between the at least two second impurity regions,

a floating gate formed over and insulated from the active region; and

a control gate formed over and insulated from the floating gate,

wherein the at least two second impurity regions ~~has~~ have a dot-like shape or an elliptical shape;

wherein the floating gate overlaps a boundary between at least one of the pair of the first impurity regions and the at least two second impurity regions.

45. (Canceled).

46. (Previously Presented) A semiconductor device according to claim 44 further comprising a substrate, wherein the semiconductor film is formed over the substrate.

47. (Canceled).

48. (Previously presented) A semiconductor device according to claim 44, wherein an electronic device mounting the semiconductor device is any one of a mobile computer, a head-mounted display, a video camera, a cellular phone, a digital camera, a rear type projector, a front type projector.

49. (Currently amended) A semiconductor device comprising:

a NAND type circuit having a plurality of one memory transistor, the memory transistor comprising:

a semiconductor film;

a pair of first impurity regions being formed in the semiconductor film;

an active region formed between the pair of first impurity regions in the semiconductor film;

at least two second impurity regions formed in said semiconductor film between the pair of first impurity regions;

at least one channel region between the at least two second impurity regions,

a floating gate formed over and insulated from the active region; and

a control gate formed over and insulated from the floating gate,

wherein the at least two second impurity regions ~~has~~ have a dot-like shape or an elliptical shape;

wherein the floating gate overlaps a boundary between at least one of the pair of the first impurity regions and the at least two second impurity regions.

50. (Canceled).

51. (Previously presented) A semiconductor device according to claim 49 further comprising a substrate, wherein the semiconductor film is formed over the substrate.

52. (Canceled).

53. (Previously presented) A semiconductor device according to claim 49, wherein an

electronic device mounting the semiconductor device is any one of a mobile computer, a head-mounted display, a video camera, a cellular phone, a digital camera, a rear type projector, a front type projector.

54. (New) A semiconductor device according to claim 24 further comprises an insulating layer that underlies the semiconductor layer, wherein the insulating layer comprises the same conductivity type impurity element as the at least two second impurity regions.

55. (New) A semiconductor device according to claim 29 further comprises an insulating layer that underlies the semiconductor layer, wherein the insulating layer comprises the same conductivity type impurity element as the at least two second impurity regions.

56. (New) A semiconductor device according to claim 34 further comprises an insulating layer that underlies the semiconductor layer, wherein the insulating layer comprises the same conductivity type impurity element as the at least two second impurity regions.

57. (New) A semiconductor device according to claim 39 further comprises an insulating layer that underlies the semiconductor layer, wherein the insulating layer comprises the same conductivity type impurity element as the at least two second impurity regions.

58. (New) A semiconductor device according to claim 44 further comprises an insulating layer that underlies the semiconductor layer, wherein the insulating layer comprises the same conductivity type impurity element as the at least two second impurity regions.

59. (New) A semiconductor device according to claim 49 further comprises an insulating layer that underlies the semiconductor layer, wherein the insulating layer comprises the same conductivity type impurity element as the at least two second impurity regions.